

SANYO

No.1580C

2SC3457

NPN Triple Diffused Planar Silicon Transistor

800V/3A Switching Regulator Applications

Features

- High breakdown voltage and high reliability.
- Fast switching speed (tf: 0.1μs typ).
- Wide ASO.
- Adoption of MBIT process.

Absolute Maximum Ratings at Ta=25°C

			unit
Collector-to-Base Voltage	V_{CB0}	1100	V
Collector-to-Emitter Voltage	V_{CE0}	800	V
Emitter-to-Base Voltage	V_{EB0}	7	V
Collector Current	I_C	3	A
Collector Current (Pulse)	I_{CP}	$PW \leq 300\mu s, \text{Duty Cycle} \leq 10\%$	10 A
Base Current	I_B	1.5	A
Collector Dissipation	P_C	$T_c = 25^\circ C$	50 W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

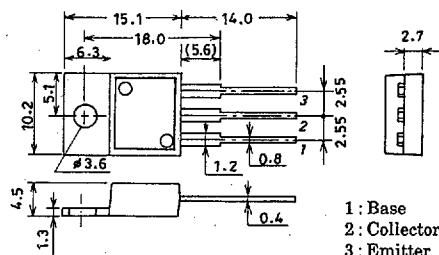
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$			10	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=0.2A$	10*		40*	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=1A$	8			
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.2A$		15		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		60		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.5A, I_B=0.3A$			2.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1.5A, I_B=0.3A$			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	1100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	800			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V

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*: The $h_{FE(1)}$ of the 2SC3457 is classified as follows. When specifying the $h_{FE(1)}$ rank, specify two ranks or more in principle.

10	K	20	15	L	30	20	M	40
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Package Dimensions 2010C
(unit:mm)

1: Base
2: Collector
3: Emitter

JEDEC: TO220AB
EIAJ: SC46

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	min	typ	max	unit
Collector-to-Emitter Sustain Voltage	800			V

Collector-to-Emitter Sustain Voltage $V_{CE(sus)}$

$I_C = 1.5A$
 $I_{B1} = -I_{B2} = 0.3A$,
 $L = 2mH$, Clamped

Turn-on Time

 t_{on}

$V_{CC} = 400V$,
 $5I_{B1} = -2.5I_{B2} = I_C = 2A$
 $R_L = 200\Omega$

0.5 μs

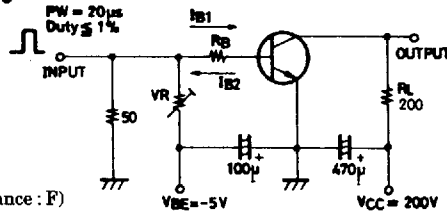
Fall Time

 t_{stg} 3.0 μs

Storage Time

 t_f 0.3 μs

Switching Time Test Circuit

Unit (Resistance : Ω , Capacitance : F)